

**REMARKS**

Claims 1-16 are now pending in the application. Claims 1, 7, 15 and 16 have been amended in the present application. The basis for the above amendments may be found throughout the specification, drawings and claims as originally filed. The Examiner is respectfully requested to consider the application in view of the amendments and remarks contained herein.

Applicant's invention is directed generally to a method for fabricating a field-effect transistor. Of interest, Applicant's claimed invention recites that "the interface level density between the semiconductor layer and the gate insulating film is no greater than  $10^{11}\text{cm}^{-2}\text{eV}^{-1}$ " in combination with other elements recited in the claims. None of the previously relied upon references teach or suggest a fabrication method for a semiconductor device having this claimed characteristic. Therefore, it is respectfully submitted that the pending claims define patentable subject matter over the previously relied upon references.

Prompt and favorable consideration of this amendment is respectfully requested. If the Examiner believes that personal communication will expedite prosecution of this application, the Examiner is invited to telephone the undersigned at (248) 641-1600.

Respectfully submitted,

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